MPPS™ Miniature Package Power Solutions 80V NPN LOW SATURATION TRANSISTOR

SUMMARY

NPN — V_{CEO} = 80V; R_{SAT} = 68m Ω ; I_{C} = 3.5A

DESCRIPTION

Packaged in the new innovative 2mm x 2mm MLP (Micro Leaded Package) outline, these new 4th generation low saturation dual PNP transistors offer extremely low on state losses making them ideal for use in DC-DC circuits and various driving and power management functions.

Additionally users gain several other **key benefits**:

Performance capability equivalent to much larger packages Improved circuit efficiency & power levels PCB area and device placement savings Lower Package Height (0.9mm nom) Reduced component count



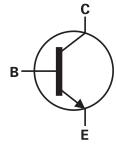
MLP322

FEATURES

- Low Equivalent On Resistance
- Extremely Low Saturation Voltage (185mV max @1A)
- h_{FF} specified up to 5A
- I_C=-3.5A Continuous Collector Current
- 2mm x 2mm MLP

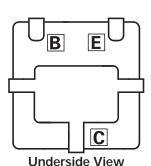
APPLICATIONS

- DC DC Converters
- DC DC Modules
- Power switches
- Motor control



ORDERING INFORMATION

DEVICE	REEL SIZE	TAPE WIDTH	QUANTITY PER REEL					
ZXTEM322TA	7″	8mm	3000					
ZXTEM322TC	13″	8mm	10000					



DEVICE MARKING

SE

SEMICONDUCTORS

ISSUE 1 - JUNE 2003

ABSOLUTE MAXIMUM RATINGS

PARAMETER	SYMBOL	LIMIT	UNIT
Collector-Base Voltage	V _{CBO}	100	V
Collector-Emitter Voltage	V _{CEO}	80	V
Emitter-Base Voltage	V _{EBO}	7.5	V
Peak Pulse Current	I _{CM}	5	А
Continuous Collector Current ^(a)	I _C	3.5	А
Base Current	I _B	1000	mA
Power Dissipation at TA=25°C ^(a) Linear Derating Factor	P _D	1.5 12	W mW/°C
Power Dissipation at TA=25°C (b) Linear Derating Factor	P _D	2.45 19.6	W mW/°C
Power Dissipation at TA=25°C ^(d) Linear Derating Factor	P _D	1 8	W mW/°C
Power Dissipation at TA=25°C ^(e) Linear Derating Factor	P_{D}	3 24	W mW/°C
Operating & Storage Temperature Range	T _j :T _{stg}	-55 to +150	°C
Junction Temperature	Tj	150	°C

THERMAL RESISTANCE

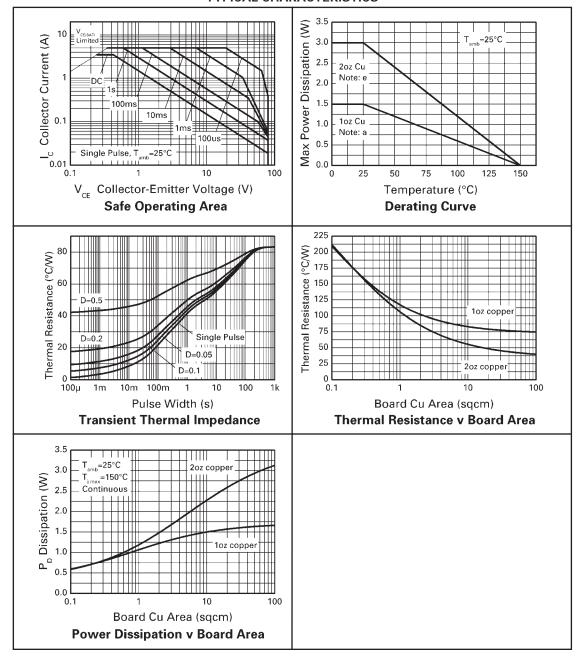
PARAMETER	SYMBOL	VALUE	UNIT				
Junction to Ambient ^(a)	$R_{\Theta JA}$	83	°C/W				
Junction to Ambient ^(b)	$R_{\Theta JA}$	51	°C/W				
Junction to Ambient ^(d)	$R_{\Theta JA}$	125	°C/W				
Junction to Ambient ^(e)	$R_{\Theta JA}$	42	°C/W				

NOTES

- (a) For a single device surface mounted on 10 sq cm 1oz copper on FR4 PCB, in still air conditions with all exposed pads attached.
- (b) For a single device surface mounted on 10 sq cm 1oz copper on FR4 PCB, in still air conditions measured at t≤5 secs with all exposed pads attached.
- $(c) \ Repetitive \ rating pulse \ width \ limited \ by \ max \ junction \ temperature. \ Refer \ to \ Transient \ Thermal \ Impedance \ graph.$
- (d) For a single device surface mounted on 10 sq cm 1oz copper FR4 PCB, in still air conditions with minimal lead connections only.
- (e) For a single device surface mounted on 65 sq cm 2oz copper FR4 PCB, in still air conditions with all exposed pads attached.
- (f) The minimum copper dimensions required for mounting are no smaller than the exposed metal pads on the base of the device, as shown in the package dimensions data. The thermal resistance for a device mounted on 1.5mm thick FR4 board using minimum copper of 1oz weight and 1mm wide tracks is Rth= 300°C/W giving a power rating of Ptot=420mW



TYPICAL CHARACTERISTICS





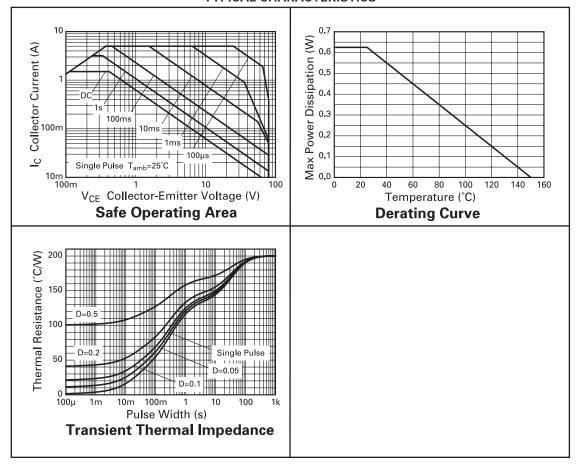
ELECTRICAL CHARACTERISTICS (at T_{amb} = 25°C unless otherwise stated)

SYMBOL	MIN.	TYP.	MAX.	UNIT	CONDITIONS
V _{(BR)CBO}	100	180		V	I _C =100μA
	80	110		V	I _C =10mA*
V _{(BR)EBO}	7.5	8.2		V	I _E =100μA
I _{CBO}			25	nA	V _{CB} =80V
I _{EBO}			25	nA	V _{EB} =6V
I _{CES}			25	nA	V _{CE} =65V
V _{CE(sat)}		15 45 145 160 240	20 60 185 200 325	mV mV mV mV	I _C =0.1A, I _B =10mA* I _C =0.5A, I _B =50mA* I _C =1A, I _B =20mA* I _C =1.5A, I _B =50mA* I _C =3.5A, I _B =300mA*
V _{BE(sat)}		1.09	1.175	V	I _C =3.5A, I _B =300mA*
		0.96	1.05	V	I _C =3.5A, V _{CE} =2V*
h _{FE}	200 300 110 60 20	450 450 170 90 30 10	900		$\begin{array}{l} I_{C} = 10 \text{mA}, \ V_{CE} = 2 \text{V}^{*} \\ I_{C} = 200 \text{mA}, \ V_{CE} = 2 \text{V}^{*} \\ I_{C} = 1A, \ V_{CE} = 2 \text{V}^{*} \\ I_{C} = 1.5 \text{A}, \ V_{CE} = 2 \text{V}^{*} \\ I_{C} = 3A, \ V_{CE} = 2 \text{V}^{*} \\ I_{C} = 5A, \ V_{CE} = 2 \text{V}^{*} \end{array}$
f _T	100	160		MHz	I _C =50mA, V _{CE} =10V f=100MHz
C _{obo}		11.5	18	pF	V _{CB} =10A, f=1MHz
t _(on)		86		ns	V _{CC} =10V, I _C =1A
t _(off)		1128		ns	$I_{B1}=I_{B2}=25\text{mA}$
	V(BR)CBO V(BR)EBO V(BR)EBO ICBO ICES VCE(sat) VBE(sat) VBE(on) hFE fT Cobo t(on)	V(BR)CBO 100 V(BR)CBO 80 V(BR)EBO 7.5 ICBO IEBO ICES VCE(sat) VBE(sat) VBE(on) hFE 200 300 110 60 20 fT 100	V(BR)CBO 100 180 V(BR)CEO 80 110 V(BR)EBO 7.5 8.2 ICBO IEBO 15 VCE(sat) 15 45 145 145 160 240 240 1.09 VBE(sat) 0.96 450 300 450 110 10 90 20 30 10 16 10 10 Cobo 11.5 11.5 t(on) 86 86	V(BR)CBO 100 180 V(BR)CEO 80 110 V(BR)EBO 7.5 8.2 ICBO 25 IEBO 25 VCE(Sat) 15 20 45 60 145 185 160 200 240 325 VBE(sat) 1.09 1.175 VBE(on) 0.96 1.05 hFE 200 450 900 10 10 160 fT 100 160 Cobo 11.5 18 t(on) 86	V(BR)CBO 100 180 V V(BR)CEO 80 110 V V(BR)EBO 7.5 8.2 V ICBO 25 nA IEBO 25 nA ICES 25 nA VCE(sat) 15 20 mV 45 60 mV mV 145 185 mV mV 240 325 mV VBE(sat) 1.09 1.175 V VBE(on) 0.96 1.05 V hFE 200 450 900 110 170 900 MHz Cobo 11.5 18 pF t(on) 86 ns

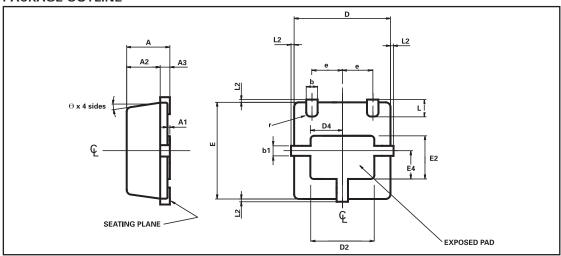
^{*}Measured under pulsed conditions. Pulse width=300 $\mu s.$ Duty cycle $\leq 2\%$



TYPICAL CHARACTERISTICS



PACKAGE OUTLINE



Controlling dimensions are in millimetres. Approximate conversions are given in inches

PACKAGE DIMENSIONS

DIM	Millimetres		Inches		DIM	Millimetres		Inches	
DIIVI	Min	Max	Min	Max	DIIVI	Min	Max	Min	Max
Α	0.80	1.00	0.0315	0.0393	е	0.65	REF	0.025	5 REF
A1	0.00	0.05	0.00	0.00 0.002 E 2.00 BSC		BSC	0.0787 BSC		
A2	0.65	0.75	0.0255	0.0295	E2	0.79	0.99	0.031	0.039
A3	0.15	0.25	0.0059	0.0098	E4	0.48	0.68	0.0188	0.0267
b	0.18	0.28	0.0070	0.0110	L	0.20	0.45	0.0078	0.0177
b1	0.17	0.30	0.0066	0.0118	L2	0.125	MAX.	0.005	REF
D	2.00 BSC 0.0787 BSC		r	0.075 BSC		0.0029 BSC			
D2	1.22	1.42	0.0480	0.0559	θ	0°	12°	0°	12°
D4	0.56	0.76	0.0220	0.0299					

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